





Features

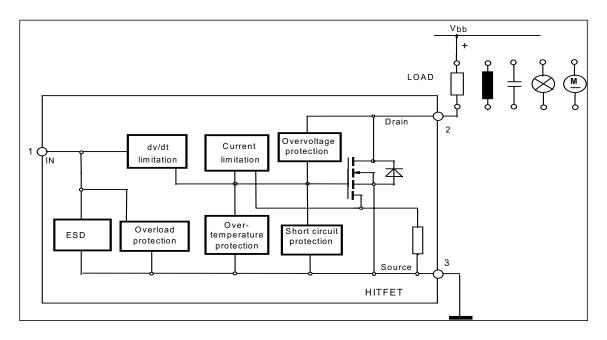
- Logic Level Input
- Input Protection (ESD)
- Thermal shutdown with latch
- Overload protection
- Short circuit protection
- Overvoltage protection
- Current limitation
- Status feedback with external input resistor
- Analog driving possible
- AEC qualified
- Green product (RoHS compliant)

Application

- All kinds of resistive, inductive and capacitive loads in switching or linear applications
- μC compatible power switch for 12 V and 24 V DC applications
- Replaces electromechanical relays and discrete circuits

General Description

N channel vertical power FET in Smart SIPMOS[®] chip on chip technology. Providing embedded protection functions.



Product Summary

Drain source voltage	$V_{\rm DS}$	60	V
On-state resistance	R _{DS(on)}	28	mΩ
Current limit	I _{D(lim)}	25	Α
Nominal load current	I _{D(ISO)}	12	Α
Clamping energy	E _{AS}	4000	mJ





Maximum Ratings at Tj = 25 °C unless otherwise specified

Parameter	Symbol	Value	Unit	
Drain source voltage	V_{DS}	60	V	
Drain source voltage for short circuit protection	V _{DS(SC)}	32		
Continuous input current 1)	I _{IN}		mA	
$-0.2V \le V_{IN} \le 10V$		no limit		
V_{IN} < -0.2V or V_{IN} > 10V		<i>I</i> _{IN} ≤ 2		
Operating temperature	T _i	- 40 +150	°C	
Storage temperature	$T_{\rm stg}$	- 55 + 150		
Power dissipation	P_{tot}	149	W	
$T_{\rm C}$ = 25 °C				
Unclamped single pulse inductive energy	E _{AS}	4000	mJ	
$I_{D(ISO)} = 12 A$				
Electrostatic discharge voltage (Human Body Model)	V _{ESD}	3000	V	
according to MIL STD 883D, method 3015.7 and				
EOS/ESD assn. standard S5.1 - 1993				
Load dump protection $V_{\text{LoadDump}}^{(2)} = V_{\text{A}} + V_{\text{S}}$	V_{LD}			
$V_{\rm IN}$ =low or high; $V_{\rm A}$ =13.5 V				
$t_d = 400 \text{ ms}, R_I = 2 \Omega, I_D = 0.5*12A$		100		
t_{d} = 400 ms, R_{I} = 2 Ω , I_{D} = 12A		84		

Thermal resistance

junction - case:	R_{thJC}	0.84	K/W
junction - ambient:	R_{thJA}	75	
SMD version, device on PCB: 3)	R_{thJA}	45	

¹In case of thermal shutdown a minimum sensor holding current of 500 µA has to be guaranteed (see also page 3).

Datasheet 2 Rev. 1.4, 2012-07-11

 $^{^2}V_{\mathsf{Loaddump}}$ is setup without the DUT connected to the generator per ISO 7637-1 and DIN 40839

 $^{^3}$ Device on 50mm*50mm*1.5mm epoxy PCB FR4 with 6cm 2 (one layer, 70 μ m thick) copper area for Drain connection. PCB mounted vertical without blown air.



Electrical Characteristics

Parameter	Symbol		Values		Unit
at T _j =25°C, unless otherwise specified		min.	typ. max.		1
Characteristics	•			•	•
Drain source clamp voltage	V _{DS(AZ)}	60	-	73	V
$T_{\rm j}$ = - 40+ 150°C, $I_{\rm D}$ = 10 mA					
Off state drain current	I _{DSS}	-	-	20	μΑ
$V_{\rm DS}$ = 32 V, $T_{\rm j}$ = -40+150 °C, $V_{\rm IN}$ = 0 V					
Input threshold voltage	V _{IN(th)}	1.3	1.7	2.2	V
$I_{\rm D}$ = 2,7 mA					
Input current - normal operation, $I_D < I_{D(lim)}$:	/IN(1)	-	35	100	μΑ
V _{IN} = 10 V					
Input current - current limitation mode, $I_D = I_{D(lim)}$:	I _{IN(2)}	-	270	500	
V_{IN} = 10 V					
Input current - after thermal shutdown, $I_D=0$ A:	/ _{IN(3)}	1000	2500	4000	
V _{IN} = 10 V					
Input holding current after thermal shutdown 1)	I _{IN(H)}				
<i>T</i> _j = 25 °C		500	-	-	
<i>T</i> _j = 150 °C		300	-	-	
On-state resistance	R _{DS(on)}				$m\Omega$
$V_{\rm IN}$ = 5 V, $I_{\rm D}$ = 12 A, $T_{\rm j}$ = 25 °C		-	31	34	
V_{IN} = 5 V, I_{D} = 12 A, T_{j} = 150 °C		-	52 68		
On-state resistance	R _{DS(on)}				
$V_{\rm IN}$ = 10 V, $I_{\rm D}$ = 12 A, $T_{\rm j}$ = 25 °C		-	25	28	
V_{IN} = 10 V, I_{D} = 12 A, T_{j} = 150 °C		-	45	56	
Nominal load current (ISO 10483)	I _{D(ISO)}	12	-	-	Α
$V_{\text{IN}} = 10 \text{ V}, V_{\text{DS}} = 0.5 \text{ V}, T_{\text{C}} = 85 \text{ °C}$					

¹If the input current is limited by external components, low drain currents can flow and heat the device. Auto restart behaviour can occur.

Datasheet 3 Rev. 1.4, 2012-07-11



Electrical Characteristics

Parameter	Symbol		Values		Unit	
at T _j =25°C, unless otherwise specified		min.	typ.	max.	1	
Characteristics	·	•	•	•	•	
Initial peak short circuit current limit	I _{D(SCp)}	-	100	-	Α	
V_{IN} = 10 V, V_{DS} = 12 V						
Current limit 1)	I _{D(lim)}	25	35	50		
V_{IN} = 10 V, V_{DS} = 12 V, t_{m} = 350 µs,						
_T _j = -40+150 °C						
Dynamic Characteristics	·	•	•			
Turn-on time V_{IN} to 90% I_{D} :	t _{on}	-	40	100	μs	
$R_{\rm L}$ = 2,2 Ω , $V_{\rm IN}$ = 0 to 10 V, $V_{\rm bb}$ = 12 V						
Turn-off time V_{IN} to 10% I_{D} :	$t_{ m off}$	-	70	170		
$R_{\rm L}$ = 2,2 Ω , $V_{\rm IN}$ = 10 to 0 V, $V_{\rm bb}$ = 12 V						
Slew rate on 70 to 50% V _{bb} :	-dV _{DS} /dt _{on}	_	1	3	V/µs	
$R_{\rm L}$ = 2,2 Ω , $V_{\rm IN}$ = 0 to 10 V, $V_{\rm bb}$ = 12 V						
Slew rate off 50 to 70% $V_{\rm bb}$:	dV _{DS} /dt _{off}	_	1	3		
$R_{\rm L}$ = 2,2 Ω , $V_{\rm IN}$ = 10 to 0 V, $V_{\rm bb}$ = 12 V						
Protection Functions ²⁾						
Thermal overload trip temperature	T _{it}	150	165	-	°C	
Unclamped single pulse inductive energy	E _{AS}				mJ	
$I_{\rm D}$ = 12 A, $T_{\rm j}$ = 25 °C, $V_{\rm bb}$ = 32 V		4000	-	-		
$I_{\rm D}$ = 12 A, $T_{\rm j}$ = 150 °C, $V_{\rm bb}$ = 32 V		900	_	-		
Inverse Diode						
Inverse diode forward voltage	V _{SD}	-	1.13	-	V	
$I_{\rm F}$ = 5*12A, $t_{\rm m}$ = 300 μ S, $V_{\rm IN}$ = 0 V						

¹Device switched on into existing short circuit (see diagram Determination of I $_{D(lim)}$). If the device is in on condition and a short circuit occurs, these values might be exceeded for max. 50 μ s.

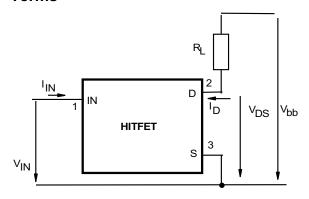
Datasheet 4 Rev. 1.4, 2012-07-11

²Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous repetitive operation

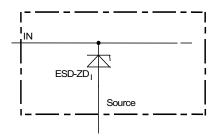


Block Diagramm

Terms

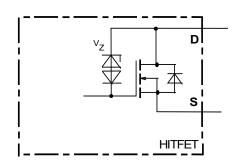


Input circuit (ESD protection)

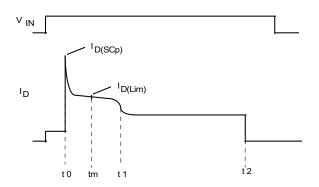


ESD zener diodes are not designed for DC current > 2 mA @ V_{IN} >10V.

Inductive and overvoltage output clamp



Short circuit behaviour



t₀: Turn on into a short circuit

t_m: Measurementpoint for I_{D(lim)}

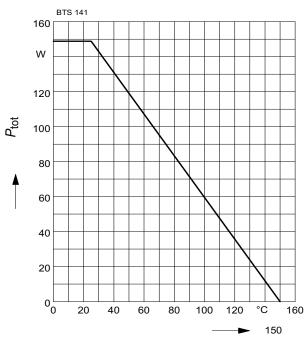
t₁: Activation of the fast temperature sensor and regulation of the drain current to a level where the junction temperature remains constant.

t₂: Thermal shutdown caused by the second temperature sensor, achieved by an integrating measurement.

Datasheet 5 Rev. 1.4, 2012-07-11

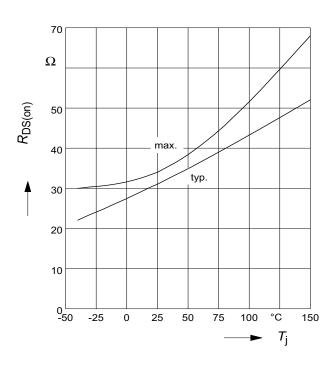


Maximum allowable power dissipation $P_{tot} = f(T_c)$



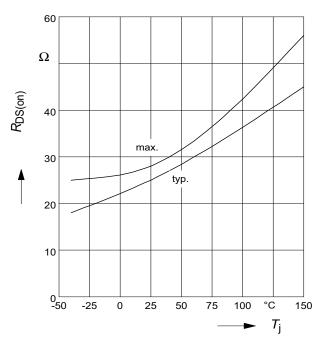
On-state resistance

$$R_{ON} = f(T_i); I_D = 12A; V_{IN} = 5V$$



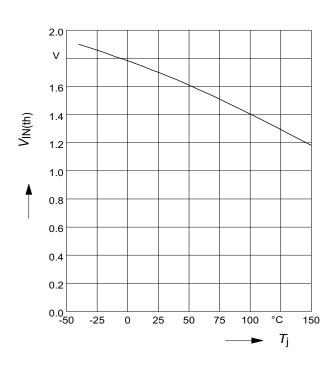
On-state resistance

$$R_{ON} = f(T_j); I_D = 12A; V_{IN} = 10V$$



Typ. input threshold voltage

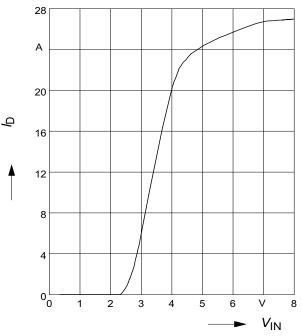
$$V_{IN(th)} = f(T_j); I_D=2,7mA; V_{DS}=12V$$





Typ. transfer characteristics

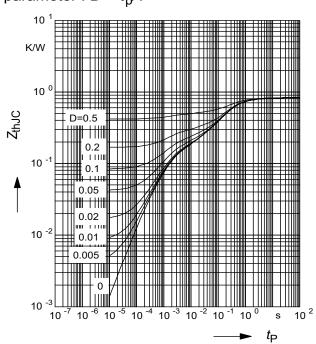
$$I_D = f(V_{IN}); V_{DS}=12V; T_j=25^{\circ}C$$



Transient thermal impedance

$$Z_{\text{thJC}} = f(t_{\text{p}})$$

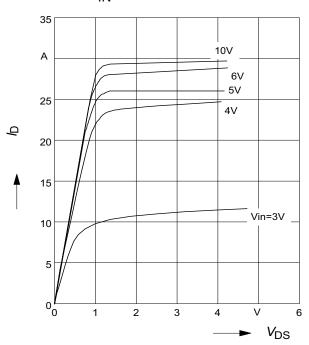
parameter : $D = t_p/T$



Typ. output characteristic

 $I_D = f(V_{DS}); T_j = 25$ °C

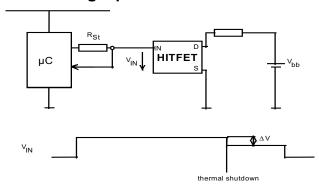
Parameter: V_{IN}





Application examples:

Status signal of thermal shutdown by monitoring input current



$$\Delta V = R_{ST} * I_{IN(3)}$$



Package Outlines

1 Package Outlines

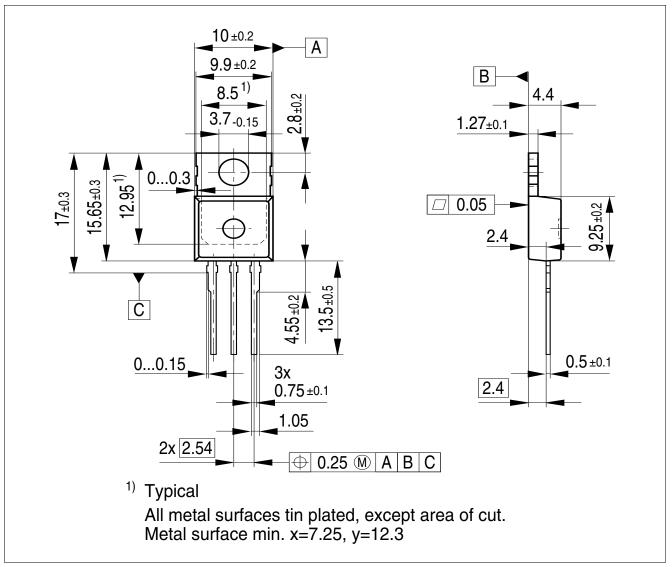


Figure 1 PG-TO220-3-1

To meet the world-wide customer requirements for environmentally friendly products and to be compliant with government regulations the device is available as a green product. Green products are RoHS-Compliant (i.e Pb-free finish on leads and suitable for Pb-free soldering according to IPC/JEDEC J-STD-020).

You can find all of our packages, sorts of packing and others in our Infineon Internet Page "Products": http://www.infineon.com/products.

Dimensions in mm



Revision History

2 Revision History

Version	Date	Changes
Rev. 1.4	2012-07-11	released through hole automotive green Datasheet
		Package drawing update, removed staggered package
		added through hole version in green package
Rev. 1.3	2008-12-10	Package drawing update
Rev. 1.2	2008-08-11	Package information updated, removed through hole version
Rev. 1.1 2008-02-22		Package parameter (humidity and climatic) removed in Maximum ratings AEC icon and RoHS icon added
		Green product and AEC qualified added to feature list
		added Protection footnote on Page 4 and changed front page general description
		Package infromation updated to green
		Green explanation added
Rev. 1.0	2000-05-19	released production version

Edition 2012-07-11

Published by Infineon Technologies AG 81726 Munich, Germany © Infineon Technologies AG 2012. All Rights Reserved.

Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics ("Beschaffenheitsgarantie"). With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation warranties of non-infringement of intellectual property rights of any third party.

Information

For further information on technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies Office (www.infineon.com).

Warnings

Due to technical requirements components may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies Office.

Infineon Technologies Components may only be used in life-support devices or systems with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system, or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body, or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.